

CXA1852N

Quadrature Modulator for 900 MHz-Band Mobile Communications

Description

The CXA1852N is an IC package that combines a $\pi/2$ phase shifter with a quadrature modulator. This is suitable for 900 MHz digital cordless telephone (CT2) and digital cellular.

Features

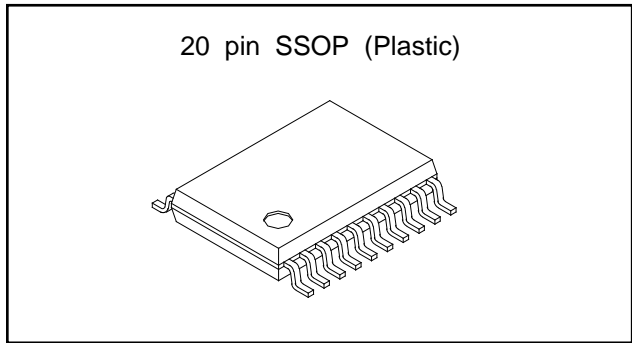
- Quadrature modulator IC has a built-in $\pi/2$ phase shifter.
- Local frequency = 300.1 MHz (max.); I&Q = 36 kHz (max.)
- Small phase error
- Operating voltage range: 2.7 to 5 V
- Power saving function
- 20-pin SSOP package used for set size reduction

Applications

- CT2 digital cordless telephone
- Digital cellular

Structure

Bipolar silicon monolithic IC



Absolute Maximum Ratings (Ta=25 °C)

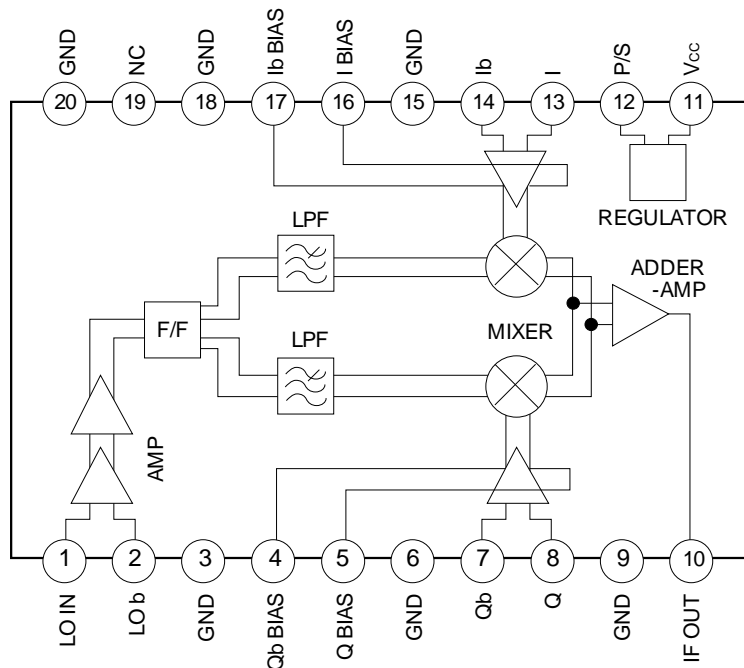
• Supply voltage	Vcc	6	V
• Operating temperature	Topr	-20 to +70	°C
• Storage temperature	Tstg	-65 to +150	°C
• Allowable power dissipation	PD	530*	mW

*When mounted on a 50 × 50 × 1.6 mm copper-foiled glass epoxy board

Recommended Operating Conditions

• Supply voltage	Vcc	2.7±5.0	V
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Block Diagram and Pin Configuration



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Pin Description

Pin No.	Symbol	Typical pin voltage (V)	Equivalent circuit	Description
1	LOCAL IN	0		Local input pin. The internal resistor provides 50 Ω matching.
2	$\overline{\text{LOCAL IN}}$	*2.0		Bias pin for the local input amplifier. Ground this pin via a capacitor.
3	GND	0		
4	$\overline{\text{Q-BIAS}}$	*0.175		Local leak level adjustment pins. Normally ground these pins via 1 kΩ resistors.
5	Q-BIAS	*0.175		
6	GND	0		
7	$\overline{\text{Q-INPU}}$	*1.85 V to 0.85 V		Q signal input pin. The input impedance is 500 kΩ or more. (Only DC signals can be normally input at the $V_{cc}/2$ DC Bias.)
8	Q-INPUT	*1.85 V to 0.85 V		Q signal input pin. The input impedance is 500kΩ or more. (Signals of up to 1 Vp-p can be input at the $V_{cc}/2$ DC Bias.)
9	GND	0		
10	IF OUTPUT	*1.4		IF output pin. (An output impedance of 50 Ω is provided by the emitter follower.)

Pin No.	Symbol	Typical pin voltage (V)	Equivalent circuit	Description
11	Vcc	5.5 to 2.7		Power supply pin.
12	POWER SAVE	0 to 5.5		Power saving control pin. OFF when $V_{P/S} \leq 1.0$ V; ON when $V_{P/S} \geq 1.8$ V
13	I-INPUT	*0.85 to 1.85		I signal input pin. The input impedance is 500 kΩ or more. (Signals of up to 1 Vp-p can be input at the $V_{cc}/2$ DC Bias.)
14	I-INPUT	*0.85 to 1.85		I signal input pin. The input impedance is 500 kΩ or more (Only DC signals can be normally input at the $V_{cc}/2$ DC Bias.)
15	GND	0		
16	I-BIAS	*0.175		Local leak level adjustment pin. Normally ground this pin via a 1 kΩ resistor.
17	I-BIAS	*0.175		
18	GND	0		
19	N.C	—		
20	GND	0		

Electrical Characteristics

(Ta=25 °C, Vcc=2.7 V, ZL=Zs=50 Ω)*

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit
Current consumption	I _{CC}	For no signal input	10	15.0	22	mA
Standby current consumption	I _{CC} (PS)	PS		330	480	μA
IF output power	P _{out}	50 Ω load, f=f _{LO} /2+f _{I/Q}	-15	-11	-7.0	dBm
Lo carrier leak	ISO (Lo)	f _{I/Q} =36 kHz, 1 V _{p-p} , f _{out} =f _{LO} /2	26	35.0		dBc
Lo leak level	P _{LO}	I/Q=V _{CC} /2, f _{out} =f _{LO} /2		-49.0	-37	dBm
Image rejection (side-band leak)	ImR	f _{out} =f _{LO} /2-f _{I/Q}	28.5	37.5		dBc
I/Q input impedance	Z _{I/Q}		500			kΩ
Power saving response time	Rise	T _{P/S} (RISE)		1.0	5.0	μs
	Fall	T _{P/S} (DOWN)		1.0	3.0	μs
Power saving control voltage		V _{P/S} (ON)	1.8		5.5	V
		V _{P/S} (OFF)			1.0	V
Lo input level	L _{in}		-17		-7	dBm

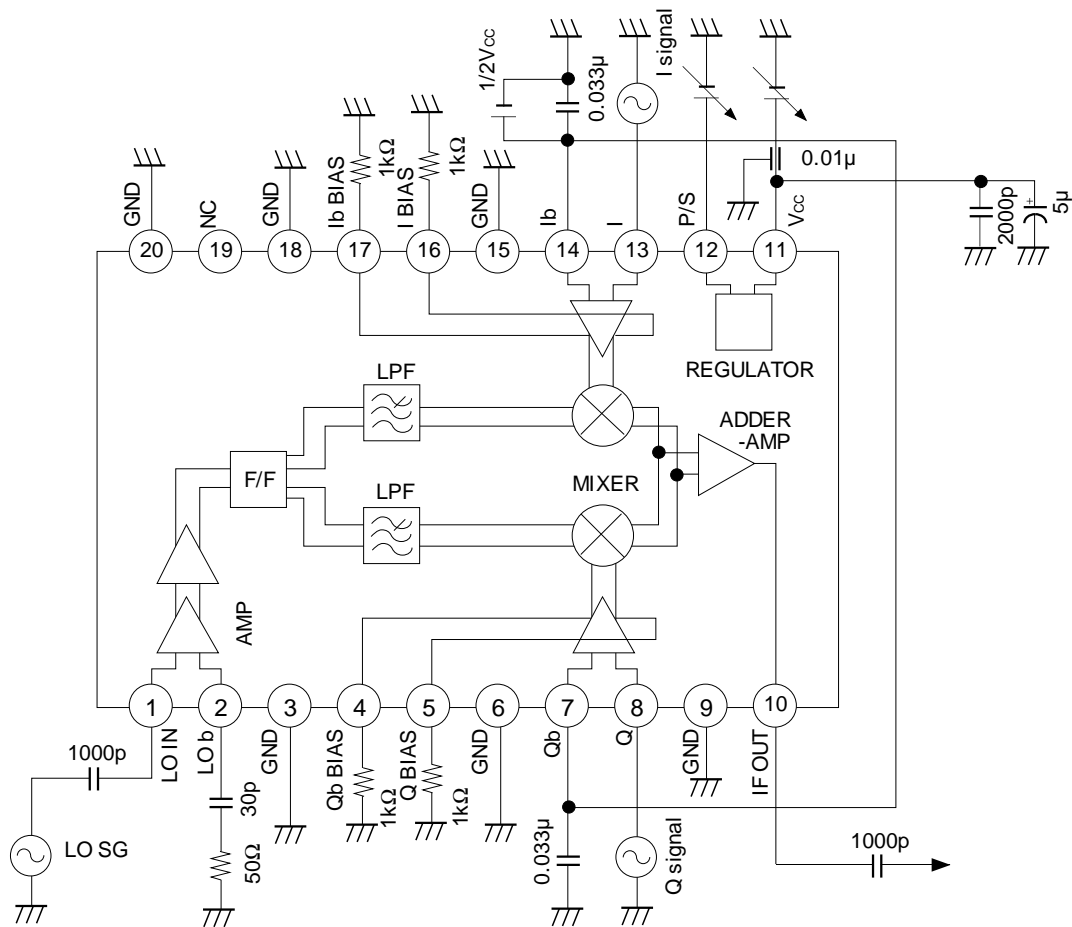
Design Reference Values

(Ta=25 °C, Vcc=2.7 V, ZL=Zs=50 Ω)*

Item	Symbol	Conditions	Typ.	Unit
I/Q third-order intermodulation distortion	IM _{3I/Q}	f _{out} =f _{LO} /2-3f _{I/Q}	37.3	dBc
Lo input VSWR			1.1	X:1
IF output VSWR			1.2	X:1

* f_{LO}=300.1 MHz Pin=-10 dBmf_{I/Q}=36 kHz 1 V_{p-p} DC=V_{CC}/2

Electrical Characteristics Test Circuit

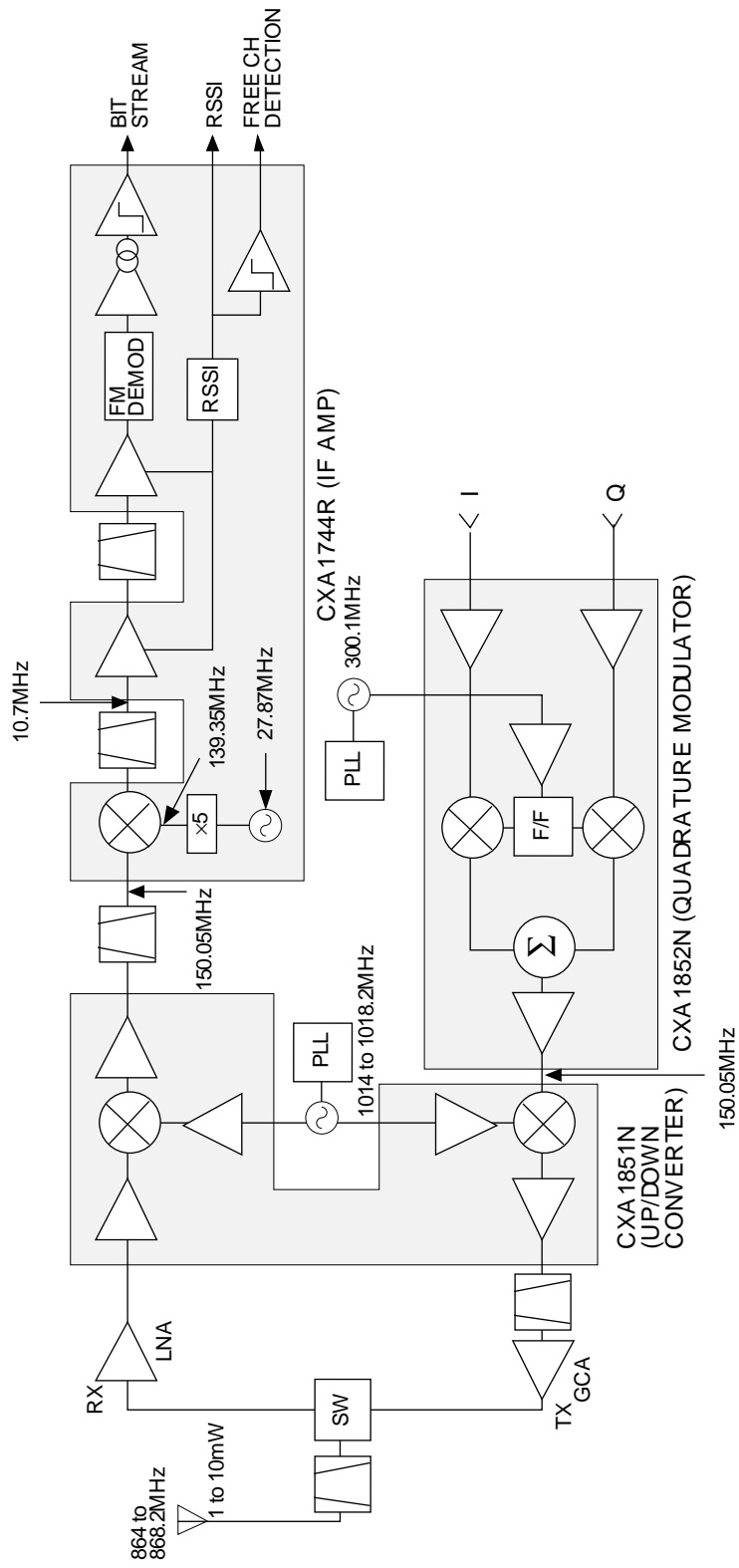


Signal	Frequency	Input level	Remarks
Lo	300.1 MHz	-10 dBm	
I signal	36 kHz	1 Vp-p	I/O phase difference = 90 °C DC for measuring the local leak
Q signal	35 kHz	1 Vp-p	

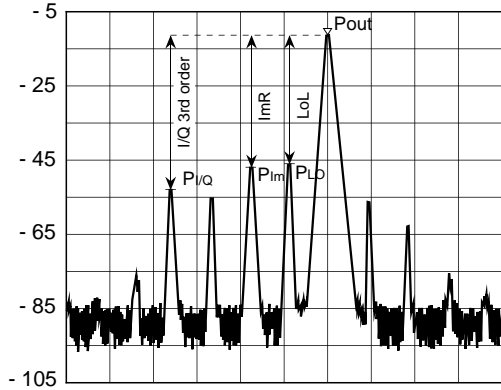
$V_{CC}=V_{P/S}$	2.7 to 5.5 V
$V_I=V_{Ib}=V_Q=V_{Qb}$	$0.5 \times V_{CC}$

Block Diagram

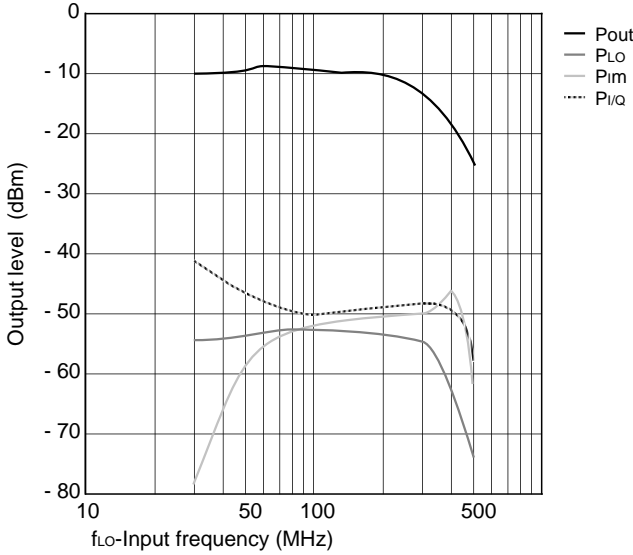
Digital cordless telephone chip set (CXA1744R/CXA1851N/CXA1852N)



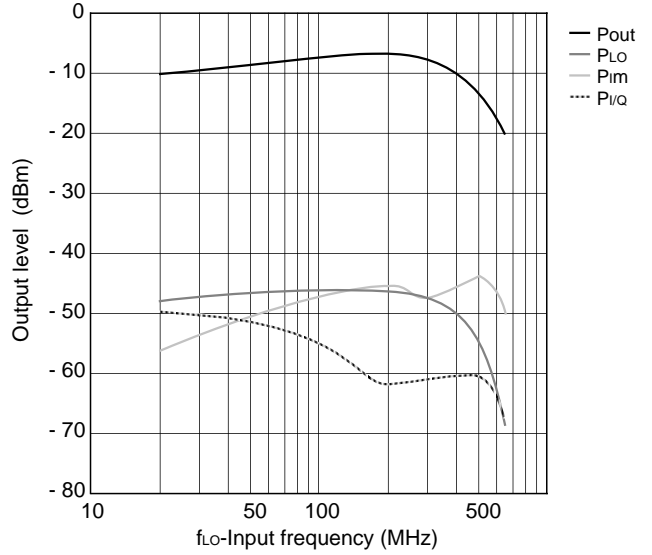
Modulation spectrum ($V_{CC}=2.7V$, S.P.A. measurement)



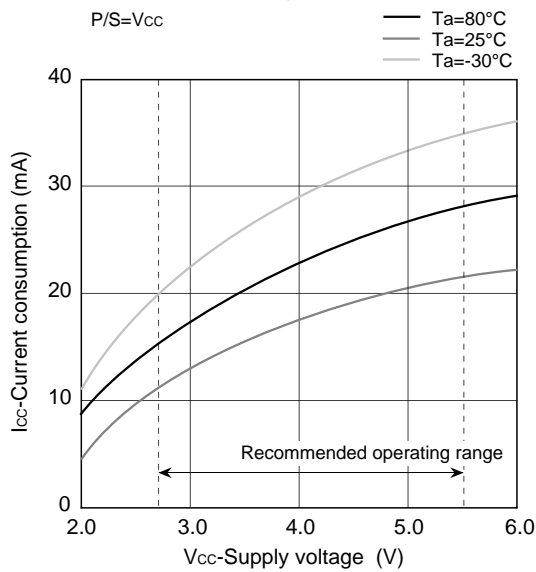
f_{LO} vs. P_{out} , P_{Lo} , P_{Im} , $P_{I/Q}$ characteristics ($V_{CC}=2.7V$)



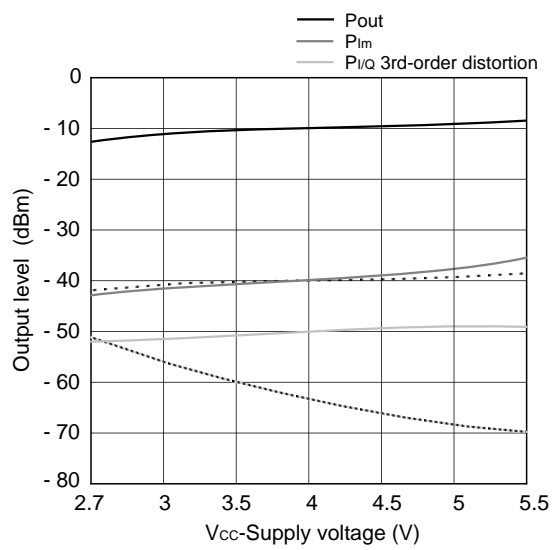
f_{LO} vs. P_{out} , P_{Lo} , P_{Im} , $P_{I/Q}$ characteristics ($V_{CC}=5.5V$)



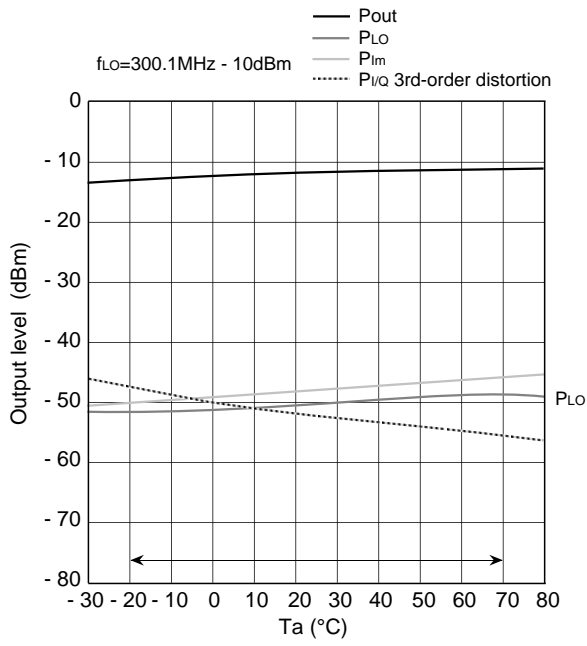
V_{CC} vs. I_{CC} characteristics
No signal input



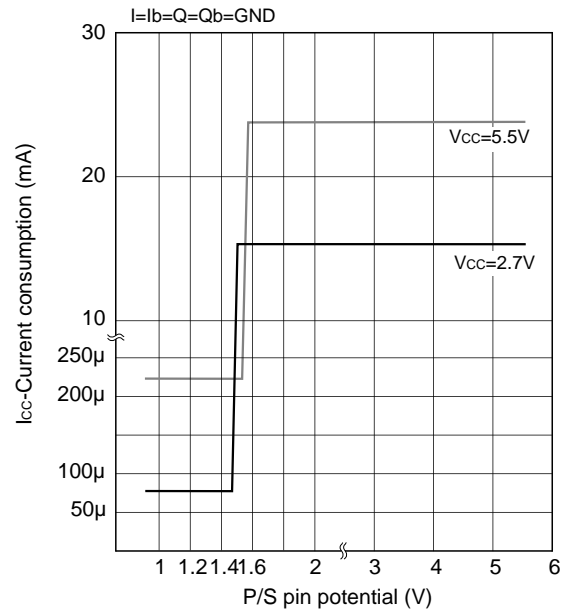
V_{CC} vs. P_{out} , P_{Im} , $P_{I/Q}$ characteristics
Lo: $f_{LO}=300.1MHz$
 $P_{in}=-10dBm$



Ta vs. Pout, PLo, PIm, P1/Q characteristics (Vcc=2.7V)



V_{P/S} vs. I_{cc} characteristics

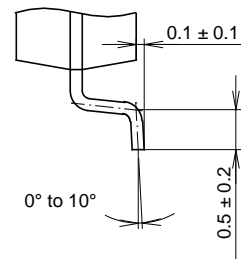
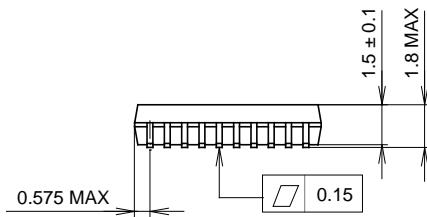
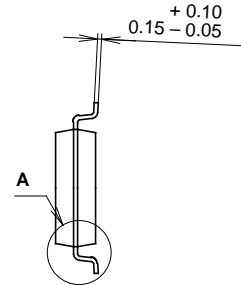
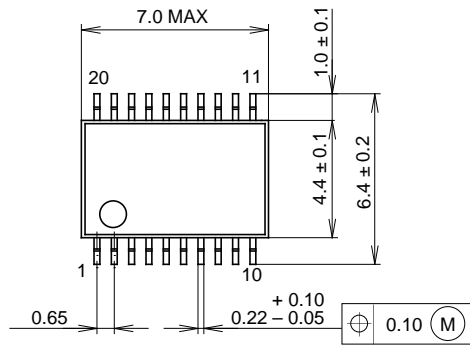


Notes on Operation

- (1) Electrostatic sensitive devices because of the high-frequency process .
- (2) Earth pattern should be as wide as possible, and do not increase ground impedance to prevent from the parasitic oscillation.
- (3) Wire the GND pin as short as possible.
- (4) Connect a by-pass capacitor to the Vcc pin.

Package Outline Unit : mm

20PIN SSOP (PLASTIC)



SONY CODE	SSOP-20P-L072
EIAJ CODE	SSOP020-P-0225-BN
JEDEC CODE	—

PACKAGE STRUCTURE

MOLDING COMPOUND	EPOXY / PHENOL RESIN
LEAD TREATMENT	SOLDER PLATING
LEAD MATERIAL	COPPER ALLOY
PACKAGE WEIGHT	0.1g